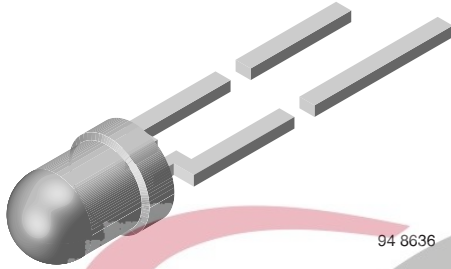


# High Power Infrared Emitting Diode, 940 nm, GaAlAs, MQW



## FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing 3$
- Peak wavelength:  $\lambda_p = 940$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 25^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



## DESCRIPTION

TSAL4400 is an infrared, 940 nm emitting diode in GaAlAs, MQW technology with high radiant power molded in a blue-gray plastic package.

## APPLICATIONS

- Infrared remote control units
- Free air transmission systems
- Infrared source for optical counters and card readers

## PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|--------------|------------------|------------|
| TSAL4400  | 36            | $\pm 25$     | 940              | 15         |

### Note

- Test conditions see table "Basic Characteristics"

## ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSAL4400      | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-1          |
| TSAL4400-RSZ  | Ammopack  | MOQ: 8000 pcs, 2000 pcs/box  | T-1          |

### Note

- MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                             | TEST CONDITION                          | SYMBOL     | VALUE       | UNIT             |
|---------------------------------------|---|------------|-------------|------------------|
| Reverse voltage                       |   | $V_R$      | 5           | V                |
| Forward current                       |   | $I_F$      | 100         | mA               |
| Peak forward current                  | $t_p/T = 0.5$ , $t_p = 100 \mu\text{s}$ | $I_{FM}$   | 200         | mA               |
| Surge forward current                 | $t_p = 100 \mu\text{s}$                 | $I_{FSM}$  | 1.5         | A                |
| Power dissipation                     |   | $P_V$      | 160         | mW               |
| Junction temperature                  |   | $T_j$      | 100         | $^\circ\text{C}$ |
| Operating temperature range           |   | $T_{amb}$  | -40 to +85  | $^\circ\text{C}$ |
| Storage temperature range             |   | $T_{stg}$  | -40 to +100 | $^\circ\text{C}$ |
| Soldering temperature                 | $t \leq 5$ s, 2 mm from case            | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction / ambient | J-STD-051, leads 7 mm, soldered on PCB  | $R_{thJA}$ | 300         | K/W              |

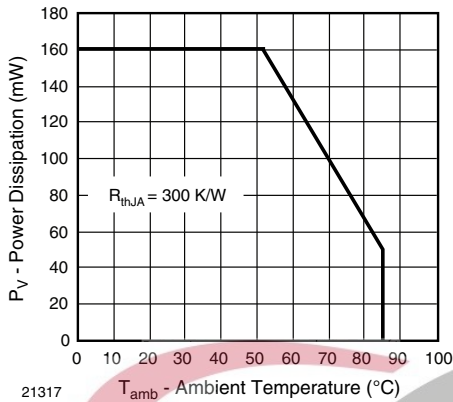


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

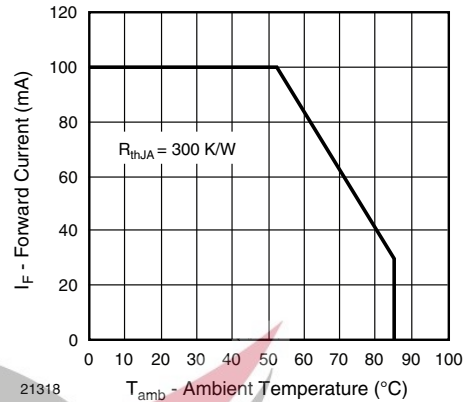


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| <b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified) |   |                  |      |          |      |               |
|---|---|------------------|------|----------|------|---------------|
| PARAMETER   | TEST CONDITION                                      | SYMBOL           | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$        | $V_F$            | -    | 1.35     | 1.6  | V             |
|   | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$ | $V_F$            | -    | 2.6      | 3    | V             |
| Temperature coefficient of $V_F$  | $I_F = 1\text{ mA}$                                 | $TK_{V_F}$       | -    | -1.8     | -    | mV/K          |
| Reverse current   | $V_R = 5\text{ V}$                                  | $I_R$            | -    | -        | 10   | $\mu\text{A}$ |
| Junction capacitance  | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$   | $C_j$            | -    | 60       | -    | pF            |
| Radiant intensity   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$        | $I_e$            | 16   | 36       | 80   | mW/sr         |
|   | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$ | $I_e$            | 135  | 290      | -    | mW/sr         |
| Radiant power   | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$        | $\phi_e$         | -    | 40       | -    | mW            |
| Temperature coefficient of $\phi_e$   | $I_F = 20\text{ mA}$                                | $TK_{\phi_e}$    | -    | -0.6     | -    | %/K           |
| Angle of half intensity   |   | $\phi$           | -    | $\pm 25$ | -    | deg           |
| Peak wavelength   | $I_F = 100\text{ mA}$                               | $\lambda_p$      | -    | 940      | -    | nm            |
| Spectral bandwidth  | $I_F = 100\text{ mA}$                               | $\Delta\lambda$  | -    | 25       | -    | nm            |
| Temperature coefficient of $\lambda_p$  | $I_F = 100\text{ mA}$                               | $TK_{\lambda_p}$ | -    | 0.25     | -    | nm/K          |
| Rise time   | $I_F = 100\text{ mA}$                               | $t_r$            | -    | 15       | -    | ns            |
| Fall time   | $I_F = 100\text{ mA}$                               | $t_f$            | -    | 15       | -    | ns            |

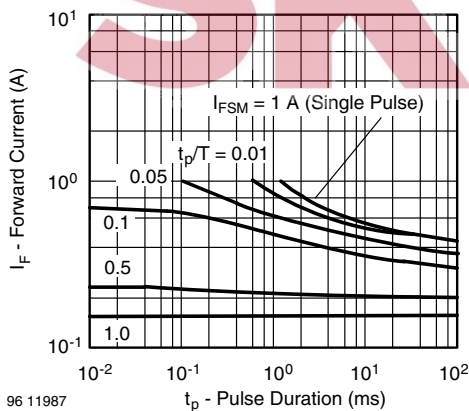
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 3 - Pulse Forward Current vs. Pulse Duration

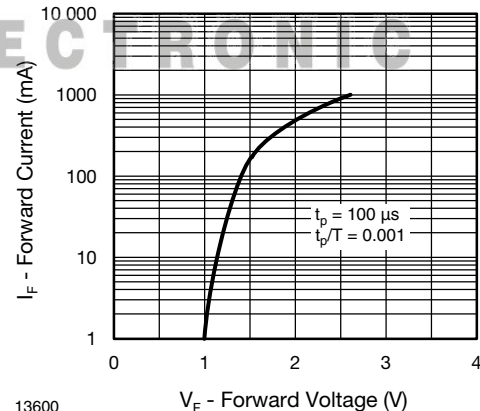


Fig. 4 - Forward Current vs. Forward Voltage

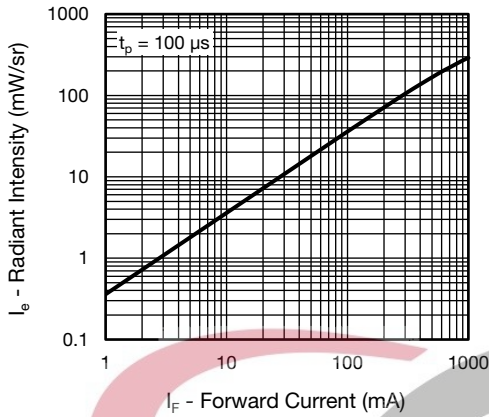


Fig. 5 - Radiant Intensity vs. Forward Current

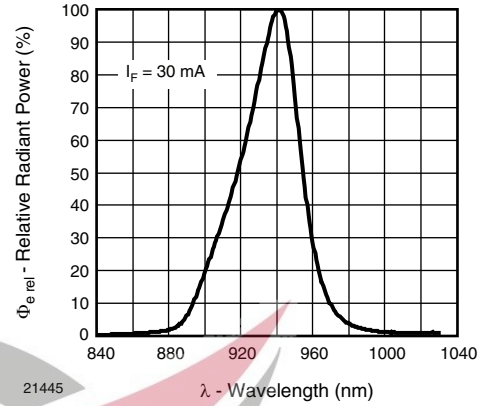


Fig. 8 - Relative Radiant Power vs. Wavelength

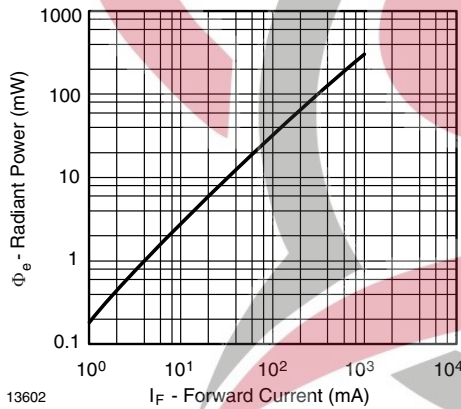


Fig. 6 - Radiant Power vs. Forward Current

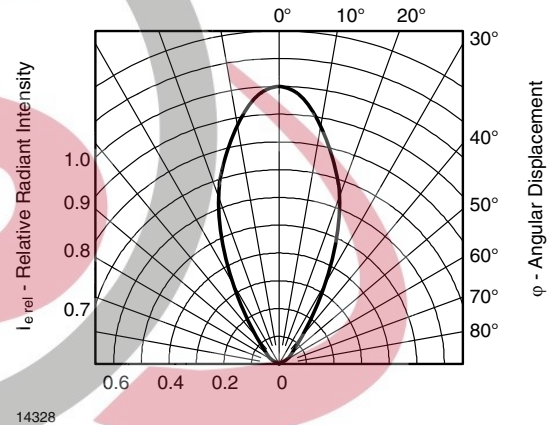


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

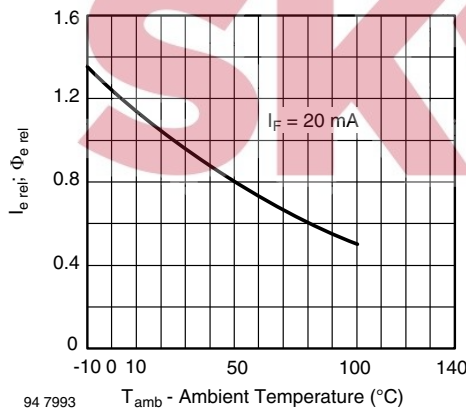
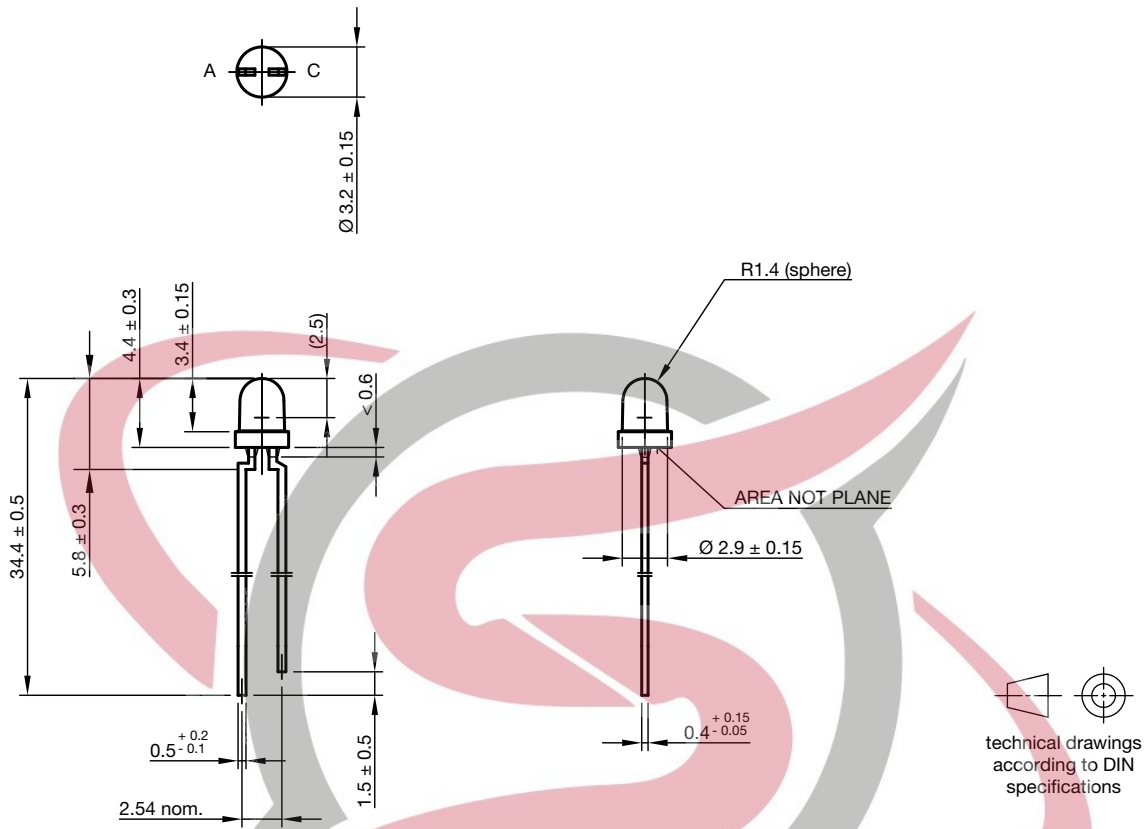


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5255.01-4  
 Issue: 9; 28.07.14





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